SF101 THRU SF107

SUPER FAST RECOVERY SILICON DIODES

Reverse Voltage - 50 to 1000 V Forward Current - 1 A

Features

- Plastic package has Underwriters Laboratory
 Flammability Classification 94V-0
- · Fast switching for high efficiency
- · High forward surge current capability

Mechanical Data

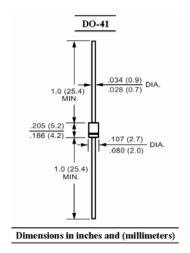
· Case: DO-41 plastic moulded

• Terminals: Axial leads, solderable per MIL-STD-202,

method 208

· Polarity: Colored band denotes cathode

• Mounting position: Any



Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half-wave, 60 Hz, resistive or inductive load, for capacitive load, derate current by 20%.

Parameter	Symbols	SF101	SF102	SF103	SF104	SF105	SF106	SF107	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current 9.5 mm Lead Length at T_A = 55 $^{\circ}$ C	I _{F(AV)}	1							Α
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load(at T_j = 125 $^{\circ}$ C)	I _{FSM}	30							Α
Maximum Forward Voltage at 1 A	V _F	1			1.25	1.4	2	.2	V
Maximum DC Reverse Current at T_a = 25 °C at Rated DC Blocking Voltage at T_a = 100 °C	I _R	5 400							μΑ
Maximum Reverse Recovery Time 1)	t _{rr}	35							ns
Typical Junction Capacitance 2)	C _j	50							pF
Typical Thermal Resistance 3)	$R_{\theta JA}$	50							°C/W
Operating Junction Temperature	Tj	- 55 to + 150							°C
Storage Temperature Range	T _{stg}	- 55 to + 150							°C

 $^{^{1)}}$ Rverse recovery test conditions: $I_{\textrm{F}}$ = 0.5 A, $I_{\textrm{R}}$ = 1 A, $I_{\textrm{rr}}$ = 0.25 A.



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 $^{^{\}rm 2)}\,\rm Measured$ at 1.0MHz and applied reverse voltage of 4 V

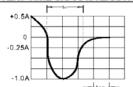
³⁾ Thermal resistance from junction ambient and from junction to lead at 9.5 mm lead length, P.C.B mounted.

FIG.1 - TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC

PEAK FORWARD SURGE CURRENT, AMPERES

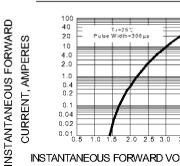


NOTES:1.RISE TIME = 7ns MAXINPUT IMPEDANCE = $1M\Omega.22pF$. 2.RISE TIME =10ns MAX.SOURCE IMPEDANCE=50 $\,\Omega$.



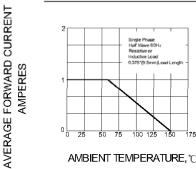
SET TIME BASE FOR 10/20 ns/cm

FIG.2 - TYPICAL FORWARD CHARACTERISTIC



INSTANTANEOUS FORWARD VOLTAGE, VOLTS

FIG.3 - FORWARD DERATING CURVE



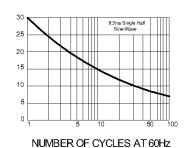
AMBIENT TEMPERATURE, ℃

FIG.4 - TYPICAL JUNCTION CAPACITANCE

JUNCTION CAPACITANCE, pF REVERSE VOLTAGE, VOLTS

FIG.6 - TYPICAL REVERSE CHARACTERISTIC

FIG.5 - PEAK FORWARD SURGE CURRENT



INSTANTANEOUS REVERSE CURRENT, MICROAMPERES 1000 100

PERCENT OF RATED PEAK REVERSE VOLTAGE, %

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